



PLD850-10-MG

Technical Data

Features

- MOCVD Pulsed Laser Diode
- Wavelength : 850 nm (Typ.)
- Peak Power : 10W (Pulsed Min)
- Threshold Current : 400mA (Typ.)
- Package Style : TO-18 (5.6 mmØ)
- Casing: Negative - Cathode

TEMPERATURE CHARACTERISTICS

DESCRIPTION	SYMBOL	RATED VALUE
Operation Temperature (°C)	T _{op}	-30 to +100
Storage Temperature (°C)	T _{stg}	-60 to +100

OPTICAL AND ELECTRICAL CHARACTERISTICS (Tc=25 °C); Test condition: 50ns, 1kHz

DESCRIPTION	SYMBOL	MIN.	TYPICAL	MAX.
Lasing Wavelength (nm)	λ_p	835	850	865
Emitting Area	A _e	-	150 x 1µm	-
Peak Power (W)	P _o	10	11	12
Threshold Current (mA)	I _{th}	450	600	700
Peak Current (A)	I _{op}	-	-	10
Peak Voltage (V)	V _{op}	-	-	7
Beam Divergence (°)	$\theta_{ }$	8	10	11
Beam Divergence ⊥ (°)	θ_{\perp}	30	40	50
Duty Factor (%)	DF	***	0.1	***

